

SLOVENSKI STANDARD

SIST EN 62276:2017

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Nadomešča:
SIST EN 62276:2013

Enokristalne rezine za površinske zvočnovalovne naprave (SAW) - Specifikacije in merilne metode (IEC 62276:2016)

Single crystal wafers for surface acoustic wave (SAW) device applications - Specifications and measuring methods (IEC 62276:2016)

Einkristall-Wafer für Oberflächenwellen-(OFW-)Bauelemente - Festlegungen und Messverfahren (IEC 62276:2016)

Tranches monocristallines pour applications utilisant des dispositifs à ondes acoustiques de surface (OAS) - Specifications et méthodes de mesure (IEC 62276:2016)

Ta slovenski standard je istoveten z: EN 62276:2016

ICS:

31.140	Piezoelektrične naprave	Piezoelectric devices
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Tranches monocristallines pour applications utilisant des
dispositifs à ondes acoustiques de surface (OAS) -
Spécifications et méthodes de mesure
(IEC 62276:2016)

Einkristall-Wafer für Oberflächenwellen-(OFW-
)Bauelemente - Festlegungen und Messverfahren
(IEC 62276:2016)

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European Committee for Electrotechnical Standardization
Comité Européen de Normalisation Electrotechnique
Europäisches Komitee für Elektrotechnische Normung

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EN 62276:2016**European foreword**

The text of document 49/1144/CDV, future edition 3 of IEC 62276, prepared by IEC/TC 49 "Piezoelectric, dielectric and electrostatic devices and associated materials for frequency control, selection and detection" was submitted to the IEC-CENELEC parallel vote and approved by CENELEC as EN 62276:2016.

The following dates are fixed:

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- latest date by which the national (dow) 2019-11-28
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IEC 61019-2	NOTE Harmonized as EN 61019-2. https://standards.iteh.ai/catalog/standards/sist/en-62276-2017
IEC 61019-3	NOTE Harmonized as EN 61019-3.
ISO 4287:1997	NOTE Harmonized as EN ISO 4287:1998.

Annex ZA (normative)

Normative references to international publications with their corresponding European publications

The following documents, in whole or in part, are normatively referenced in this document and are indispensable for its application. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

NOTE 1 When an International Publication has been modified by common modifications, indicated by (mod), the relevant EN/HD applies.

NOTE 2 Up-to-date information on the latest versions of the European Standards listed in this annex is available here: www.cenelec.eu.

<u>Publication</u>	<u>Year</u>	<u>Title</u>	<u>EN/HD</u>	<u>Year</u>
IEC 60758	2016	Synthetic Quartz Crystal - Specifications and guidelines for use	EN 60758	2016
ISO 2859-1	1989	Sampling procedures for inspection by attributes; part_1: sampling plans indexed by acceptable quality level (AQL) for lot-by-lot inspection	-	-

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IEC 62276

Edition 3.0 2016-10

INTERNATIONAL STANDARD

**Single crystal wafers for surface acoustic wave (SAW) device applications –
Specifications and measuring methods**

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CONTENTS

FOREWORD	5
INTRODUCTION	7
1 Scope	8
2 Normative references	8
3 Terms and definitions	8
3.1 Single crystals for SAW wafer	8
3.2 Terms and definitions related to LN and LT crystals	9
3.3 Terms and definitions related to all crystals	9
3.4 Flatness	10
3.5 Definitions of appearance defects	12
3.6 Other terms and definitions	13
4 Requirements	14
4.1 Material specification	14
4.1.1 Synthetic quartz crystal	14
4.1.2 LN	15
4.1.3 LT	15
4.1.4 LBO, LGS	15
4.2 Wafer specifications	15
4.2.1 General	15
4.2.2 Diameters and tolerances	15
4.2.3 Thickness and tolerance	15
4.2.4 Orientation flat	15
4.2.5 Secondary flat	16
4.2.6 Back surface roughness	16
4.2.7 Warp	16
4.2.8 TV5 or TTV	16
4.2.9 Front (propagation) surface finish	17
4.2.10 Front surface defects	17
4.2.11 Surface orientation tolerance	18
4.2.12 Inclusions	18
4.2.13 Etch channel number and position of seed for quartz wafer	18
4.2.14 Bevel	18
4.2.15 Curie temperature and tolerance	18
4.2.16 Lattice constant	18
4.2.17 Bulk resistivity (conductivity) for reduced LN and LT	19
5 Sampling plan	19
5.1 General	19
5.2 Sampling	19
5.3 Sampling frequency	19
5.4 Inspection of whole population	19
6 Test methods	19
6.1 Diameter	19
6.2 Thickness	20
6.3 Dimension of OF	20
6.4 Orientation of OF	20
6.5 TV5	20

6.6	Warp.....	20
6.7	TTV	20
6.8	Front surface defects	20
6.9	Inclusions	20
6.10	Back surface roughness.....	20
6.11	Orientation	20
6.12	Curie temperature	20
6.13	Lattice constant	20
6.14	Bulk resistivity.....	21
7	Identification, labelling, packaging, delivery condition	21
7.1	Packaging	21
7.2	Labelling and identification.....	21
7.3	Delivery condition	21
8	Measurement of Curie temperature.....	21
8.1	General.....	21
8.2	DTA method.....	21
8.3	Dielectric constant method.....	22
9	Measurement of lattice constant (Bond method)	23
10	Measurement of face angle by X-ray.....	24
10.1	Measurement principle.....	24
10.2	Measurement method	25
10.3	Measuring surface orientation of wafers.....	25
10.4	Measuring OF flat orientation.....	25
10.5	Typical wafer orientations and reference planes.....	25
11	Measurement of bulk resistivity.....	26
11.1	Resistance measurement of a wafer	26
11.2	Electrode	27
11.3	Bulk resistivity.....	27
12	Visual inspections – Front surface inspection method.....	27
Annex A (normative)	Expression using Euler angle description for piezoelectric single crystals	29
A.1	Wafer orientation using Euler angle description	29
Annex B (informative)	Manufacturing process for SAW wafers	32
B.1	Crystal growth methods	32
B.1.1	Czochralski growth method.....	32
B.1.2	Vertical Bridgman method.....	34
B.2	Standard mechanical wafer manufacturing.....	35
B.2.1	Process flow-chart	35
B.2.2	Cutting both ends and cylindrical grinding.....	36
B.2.3	Marking orientation	37
B.2.4	Slicing	37
B.2.5	Double-sided lapping	37
B.2.6	Bevelling (edge rounding).....	37
B.2.7	Mirror polishing.....	37
Bibliography	38

Figure 1 – Wafer sketch and measurement points for TV5 determination 10

Figure 2 – Schematic diagram of TTV 11

Figure 3 – Schematic diagram of warp	11
Figure 4 – Schematic diagram of Sori.....	11
Figure 5 – Example of site distribution for LTV measurement.....	12
Figure 6 – LTV value of each site.....	12
Figure 7 – Schematic of a DTA system	22
Figure 8 – Schematic of a dielectric constant measurement system	22
Figure 9 – The Bond method.....	24
Figure 10 – Measurement method by X-ray.....	24
Figure 11 – Relationship between cut angle and lattice planes	25
Figure 12 – Measuring circuit.....	26
Figure 13 – Resistance measuring equipment.....	26
Figure 14 – Shape of electrode	27
Figure A.1 – Definition of Euler angles to rotate coordinate system (X, Y, Z) onto (x_1, x_2, x_3).....	29
Figure A.2 – SAW wafer coordinate system	30
Figure A.3 – Relationship between the crystal axes, Euler angles, and SAW orientation for some wafer orientations.....	31
Figure B.1 – Czochralski crystal growth method.....	32
Figure B.2 – Example of non-uniformity in crystals grown from different starting melt compositions.....	34
Figure B.3 – Schematic of a Vertical Bridgman furnace and example of temperature distribution.....	35
Figure B.4 – Process flow-chart.....	36
Table 1 – Description of wafer orientations	14
Table 2 – Roughness, warp, TV5 and TTV specification limits	17
Table 3 – Maximum number of etch channels in seed position	18
Table 4 – Crystal planes to determine surface and OF orientations.....	25
Table 5 – Electrode size	27
Table A.1 – Selected SAW substrate orientations and corresponding Euler angles	30

INTERNATIONAL ELECTROTECHNICAL COMMISSION

SINGLE CRYSTAL WAFERS FOR SURFACE ACOUSTIC WAVE (SAW) DEVICE APPLICATIONS – SPECIFICATIONS AND MEASURING METHODS

FOREWORD

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International Standard IEC 62276 has been prepared by IEC technical committee 49: Piezoelectric, dielectric and electrostatic devices and associated materials for frequency control, selection and detection.

This third edition cancels and replaces the second edition of IEC 62276 published in 2012. It constitutes a technical revision.

This edition includes the following significant technical changes with respect to the previous edition:

- Corrections of Euler angle indications in Table 1 and axis directions in Figure 3.
- Definition of "twin" is not explained clearly enough in 3.3.3. Therefore it is revised by a more detailed definition.
- Etch channels maximum number at quartz wafer of seed which do not pass through from surface to back surface are classified for three grades in 4.2.13 a). Users use seed portions of quartz wafers for devices. They request quartz wafers with less etch channels

in seeds to reduce defects of devices. The classification of etch channels in seed may prompt a rise in quartz wafer quality.

The text of this standard is based on the following documents:

CDV	Report on voting
49/1144/CDV	49/1170/RVC

Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

This publication has been drafted in accordance with the ISO/IEC Directives, Part 2.

The committee has decided that the contents of this publication will remain unchanged until the stability date indicated on the IEC website under "<http://webstore.iec.ch>" in the data related to the specific publication. At this date, the publication will be

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INTRODUCTION

A variety of piezoelectric materials are used for surface acoustic wave (SAW) filter and resonator applications. Prior to an IEC meeting in 1996 in Rotterdam, wafer specifications were typically negotiated between users and suppliers. During this meeting, a proposal was announced to address wafer standardization. This standard has been prepared in order to provide industry standard technical specifications for manufacturing piezoelectric single crystal wafers to be used in surface acoustic wave devices.

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